

Silicon PNP Power Transistors

2SB1192

DESCRIPTION

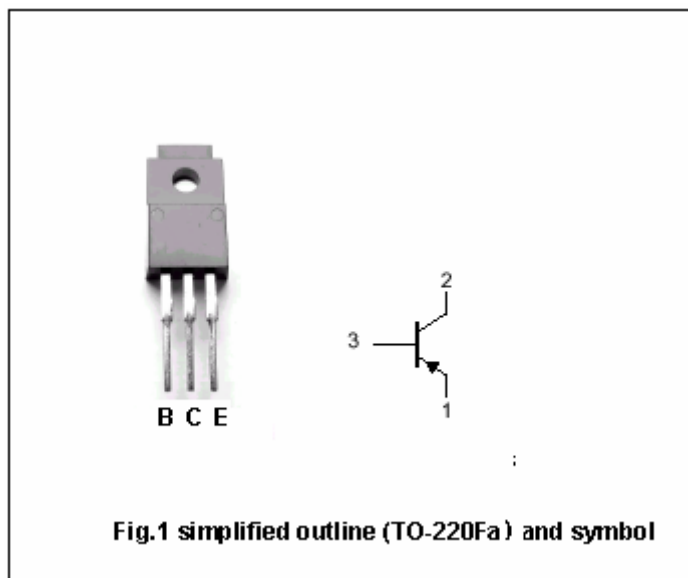
- With TO-220Fa package
- High V_{CEO}
- Large P_C
- Complement to type 2SD1770

APPLICATIONS

- Power amplifier
- TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1	A
I_{CM}	Collector current-peak		-2	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	2	W
		$T_C=25^\circ\text{C}$	25	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-5mA, I_B=0$	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-0.5mA, I_C=0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-500mA; I_B=-50mA$			-1.0	V
V_{BE}	Base-emitter on voltage	$I_C=-300mA; V_{CE}=-10V$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-200V; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-4V; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-100mA; V_{CE}=-10V$	60		240	
h_{FE-2}	DC current gain	$I_C=-300mA; V_{CE}=-10V$	50			
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V, f=1MHz$		35		pF
f_T	Transition frequency	$I_C=-100mA; V_{CE}=-10V$		20		MHz

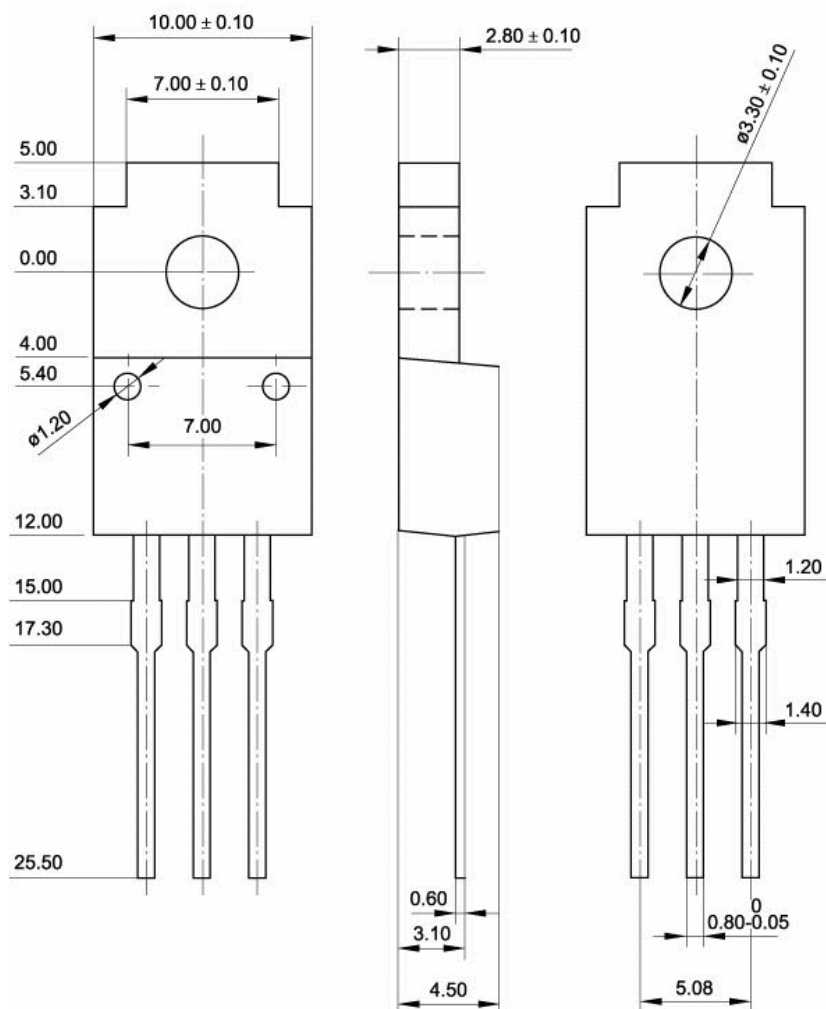
◆ h_{FE-1} Classifications

Q	P
60-140	100-240

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PACKAGE OUTLINE

Fig.2 Outline dimensions(unindicated tolerance: ± 0.15 mm)